# 2SD1835

## **Bipolar Transistor** 50V, 2A, Low VCE(sat), NPN Single NP



#### **Applications**

· Voltage regulators, relay drivers, lamp drivers, electrical equipment

#### Features

- Adoption of FBET, MBIT processes
- Large current capacity
- Low collector-to-emitter saturation voltage
- Fast switching time

#### **Specifications**

#### Absolute Maximum Ratings at Ta=25°C

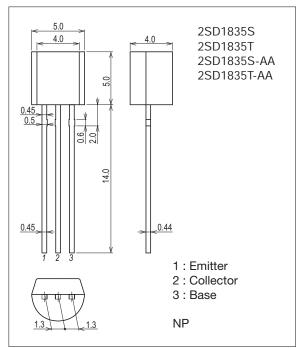
Symbol	Conditions	Ratings	Unit
VCBO		60	V
VCEO		50	V
VEBO		6	V
IC		2	А
ICP		3	Α
PC		0.75	W
Tj		150	°C
Tstg		-55 to +150	°C
	VCBO VCEO VEBO IC ICP PC Tj	VCBO   VCEO   VEBO   IC   ICP   PC   Tj	VCBO 60   VCEO 50   VEBO 6   IC 2   ICP 33   PC 0.75   Tj 150

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

#### Package Dimensions

unit : mm (typ)

7522-002



#### Product & Package Information

• Package : NP

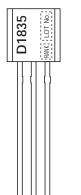
: SC-34A, TO-92, TO-226AA, SOT-54

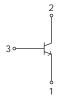
• Minimum Packing Quantity : 1,500 pcs./box, 500pcs./bag

#### Marking

• JEITA, JEDEC

**Electrical Connection** 





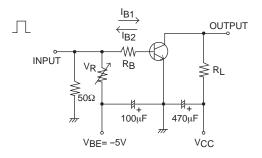
#### Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions			Unit	
Parameter	Symbol	Conditions	min	typ	max	UTIIL
Collector Cutoff Current	ICBO	VCB=50V, IE=0A			100	nA
Emitter Cutoff Current	IEBO	V <sub>EB</sub> =4V, I <sub>C</sub> =0A			100	nA
DC Current Gain	h <sub>FE</sub> 1	V <sub>CE</sub> =2V, I <sub>C</sub> =100mA	100*		560*	
	h <sub>FE</sub> 2	V <sub>CE</sub> =2V, I <sub>C</sub> =1.5A	40			
Gain-Bandwidth Product	fT	VCE=10V, IC=50mA		150		MHz
Output Capacitance	Cob	V <sub>CB</sub> =10V, f=1MHz		12		pF
Collector-to-Emitter Saturation Voltage	V <sub>CE</sub> (sat)	IC=1A, IB=50mA		0.15	0.4	V
Base-to-Emitter Saturation Voltage	V <sub>BE</sub> (sat)	IC=1A, IB=50mA		0.9	1.2	V
Collector-to-Base Breakdown Voltage	V(BR)CBO	IC=10μΑ, IE=0A	60			V
Collector-to-Emitter Breakdown Voltage	V(BR)CEO	IC=1mA, RBE=∞	50			V
Emitter-to-Base Breakdown Voltage	V(BR)EBO	IE=10μA, IC=0A	6			V
Turn-ON Time	ton			60		ns
Storage Time	tstg	See specified Test Circuit.		550		ns
Fall Time	tf			30		ns

 $^{\star}$  : The 2SD1835 is classified by 100mA hFE as follows :

Rank	R	S	Т	U
hFE	100 to 200	140 to 280	200 to 400	280 to 560

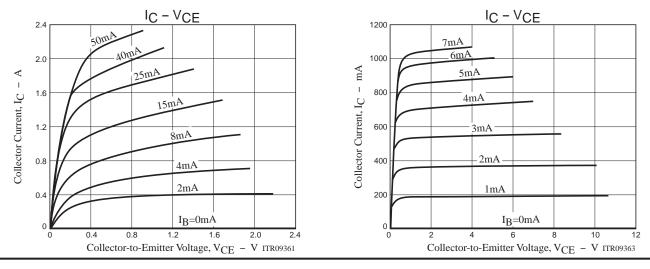
#### Switching Time Test Circuit

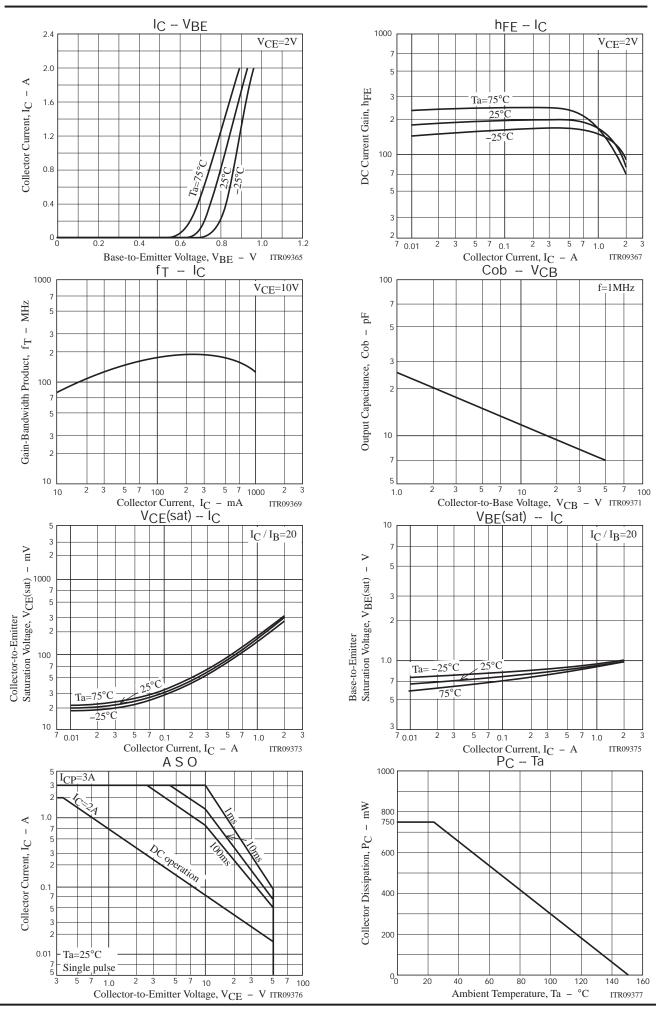


 $I_{C}=10I_{B1}=-10I_{B2}=500mA, V_{CC}=25V$ 

#### **Ordering Information**

Device	Package	Shipping	memo
2SD1835S	NP	500pcs./bag	
2SD1835T	NP	500pcs./bag	Pb Free
2SD1835S-AA	NP	1,500pcs./box	PDFlee
2SD1835T-AA	NP	1,500pcs./box	

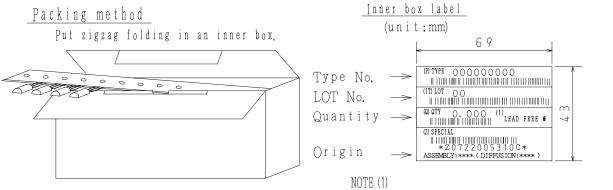




#### Taping Specification 2SD1835S-AA, 2SD1835T-AA

1. Packing Format

Package Name	Packing Type	Maximum Number of devices contained (pcs) Inner BOX (C-2) number of contained	Packing format Outer BOX (C-6)
N P	ΑA	Dimensions:nm (external) $1, 500$ $330 \times 45 \times 145$	16 inner boxes contained (24,000pcs) Dimensions:mm (external) 5 8 5 × 3 4 5 × 2 0 0

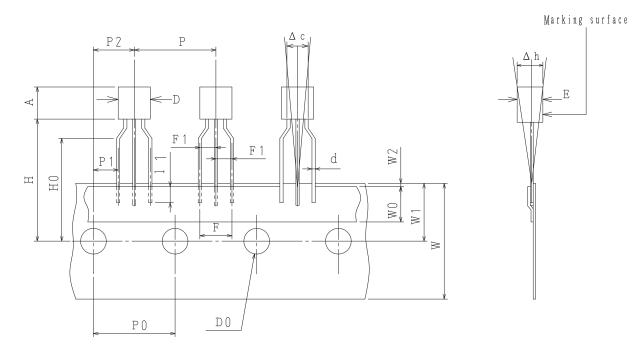


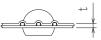
NOTE (1) The LEAD FREE \* description shows that the surface treatment of the terminal is lead free.

Label	JEITA Phase
LEAD FREE 3	JEITA Phase 3A
LEAD FREE 4	JEITA Phase 3

2. Taping specifications

2-1. Carrier tape size





2-2. Taping size standard

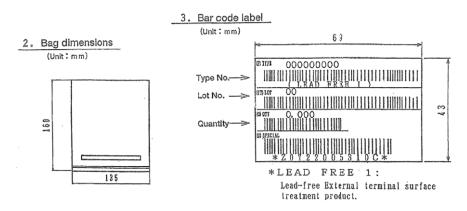
#### unit:mm

[ t e m	Symbol	Standard	Tolerance		Item	Symbol	Standard	Tolerance
Work piece outside diameter	D	50	±0.2		Tape width	W	18.0	+1.0 -0.5
WOLV DIECE ONTRINE ALUMETEL	E	4.0	±0.2		Adhesive tape	WO	60	±1.5
Work piece height	А	5.0	±0.2		Displacement of perforations		9.0	±0.5
Lead wire diameter	d	0.45×0.44t	±0. 1		Work piece bottom surface position	Η	19, 0	±1.0
Bonded lead wire	1 1	2. OMIN			Insert stopper position	ΗΟ	16.0	±0.5
Pitch between products	Р	12.7	±0.5		Work piece upper limit position	Η1	24, 5	±1.5
Pitch between perforations	Ρ0	12.7	±0.2		Perforations diameter	D ()	φ4. ()	±0.2
Distance between lead wire	F	5.0	+0.8 -0.2		Tape thickness	t	06	±0.2
Lead wire pitch distance	F 1	2.5	+0.2		Product inclination	$\triangle$ C	0	±1.0
Product inclination	riangle h	0	±2.0					
Displacement of perforations	P 1	3, 85	±0.3	Me th	asurement position is e bottom of the clinch			
	P 2	6 35	±0.3					
Displacement of tape	W 2	0. 5MAX			t to be displaced to e outside of the board			

#### Bag Packing Specification 2SD1835S, 2SD1835T

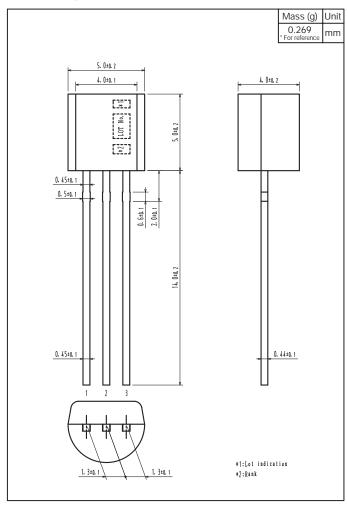
#### 1 . Packing condition

Storange package		Maximum number of devices contained (pcs.)			Packing condition			
	outline name	Bags	Inner box	Devices contained	Outer box (	A-1	)	Outer box ( $A-2$ )
	NP	500	$\begin{array}{c} B-1 \text{ Inner box dimensions :} \\ mm \text{ (external)} \\ 4 4 5 \times 2 2 5 \times 5 5 \end{array}$		5 inner boxes Outer box din 470 × 250 ×	nensions : i	mm (external)	3 inner boxes contained 30, 00 Outer box dimensions : mm (external) 470 × 250 × 190



Outline Drawing

2SD1835S, 2SD1835T



2SD1835

ON Semiconductor and the ON logo are registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of SCILLC's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typical" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

### **X-ON Electronics**

Largest Supplier of Electrical and Electronic Components

Click to view similar products for Bipolar Transistors - BJT category:

Click to view products by ON Semiconductor manufacturer:

Other Similar products are found below :

619691C MCH4017-TL-H BC546/116 BC556/FSC BC557/116 BSW67A HN7G01FU-A(T5L,F,T NJVMJD148T4G NSVMMBT6520LT1G NTE187A NTE195A NTE2302 NTE2330 NTE2353 NTE316 NTE63 NTE65 C4460 SBC846BLT3G 2SA1419T-TD-H 2SA1721-O(TE85L,F) 2SA1727TLP 2SA2126-E 2SB1202T-TL-E 2SB1204S-TL-E 2SC5488A-TL-H 2SD2150T100R SP000011176 FMC5AT148 2N2369ADCSM 2SB1202S-TL-E 2SC2412KT146S 2SC4618TLN 2SC5490A-TL-H 2SD1816S-TL-E 2SD1816T-TL-E CMXT2207 TR CPH6501-TL-E MCH4021-TL-E TTC012(Q) BULD128DT4 DDTC114EUAQ-7-F NJL0281DG NSS20500UW3TBG 732314D CMXT3906 TR CPH3121-TL-E CPH6021-TL-H SZT1010T1G 873787E